

A1
cont.

refraction at the prism 5. Thus the polarization beam combiner 7 arranged behind the prism 5 may be easily made, and at the same time the size of the polarization beam combiner 7 may be made smaller to obtain the smaller semiconductor laser module M1.--

Page 38, line 14 through page 39, line 1, please replace as follows:

A2

--In addition, through the semiconductor laser element 2 had been provided with the embedded InP type BH structure in the examples explained above, the laser element 2 may be, for example, of a GaAs ridge waveguide type as shown in Fig. 10. As shown in Fig. 10, an n type lower clad layer 41, an active layer 42, a p type upper clad layer 43, an insulation layer 44, and a p-GaAs layer 45 are laminated on the substrate 40 which comprises n-GaAs, and two ridge sections are formed in the semiconductor laser element 2. An upper electrode (p electrode) 46 is formed on the insulation layer 44 and the p-GaAs layer 45, and an lower electrode (n electrode) 47 is formed on the bottom surface of the substrate 40. --
